CHENMKO ENTERPRISE CO.,LTD

CH740H-40GP

SURFACE MOUNT
SCHOTTKY BARRIER DIODE
VOLTAGE 40 Volts CURRENT 0.04 Ampere

Halogens free devices

APPLICATION
* Low barrier diode for detectors up to GHz frequencies

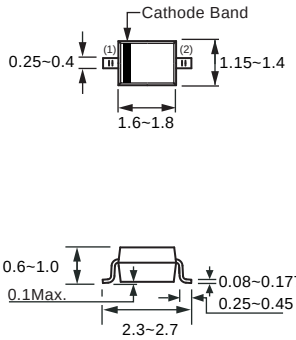
FEATURE
* Small surface mounting type. (SC-76/SOD-323)
* Low VF and low IR
* High reliability

CONSTRUCTION
* Silicon epitaxial planar

MARKING
* JC

CIRCUIT

SC-76/SOD-323



Dimensions in millimeters

SC-76/SOD-323

MAXIMUM RATINGES (At T_A = 25°C unless otherwise noted)

RATINGS	SYMBOL	CH740H-40GP			UNITS
		MIN.	TYP.	MAX.	
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	-	-	40	Volts
Maximum Average Forward Rectified Current	I_O	-	-	40	mAmps
Total Power Dissipation, T_S< 85 °C	P_{TOT}	-	-	150	mW
Typical Series Inductance	L_S	-	1.8	-	nH
Typical Case Capacitance	C_C	-	0.1	-	pF
Typical Junction Capacitance between Terminal (Note 1)	C_J	-	0.35	0.6	pF
Typical Differential Resistance (Note 2)	R_D	-	225	-	kΩ
Operating and Storage Temperature Range	T_J,T_{STG}	-55	-	+150	°C

ELECTRICAL CHARACTERISTICS (At T_A = 25°C unless otherwise noted)

CHARACTERISTICS	SYMBOL	CH740H-40GP			UNITS
		MIN.	TYP.	MAX.	
Maximum Instantaneous Forward Voltage at I_F= 2mA	V_F	-	0.58	1.00	Volts
Maximum Average Reverse Current at V_R= 40V	I_R	-	-	10	uAmps

NOTES : 1. Measured at 1.0 MHz and applied reverse voltage of 0 volts.
2. Measured at 1.0 KHz and applied reverse voltage of 0 volts.
2. ESD sensitive product handling required.

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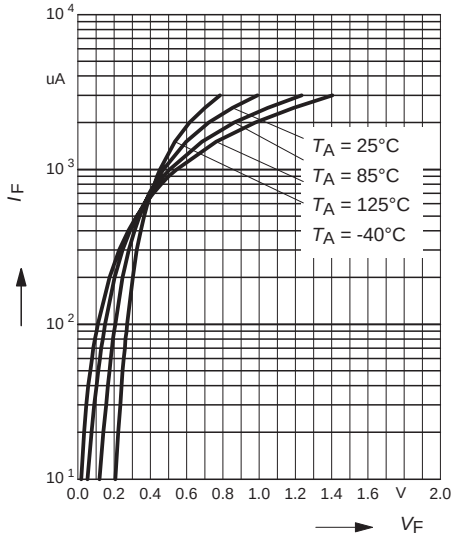
RATING CHARACTERISTIC CURVES (CH740H-40PT)

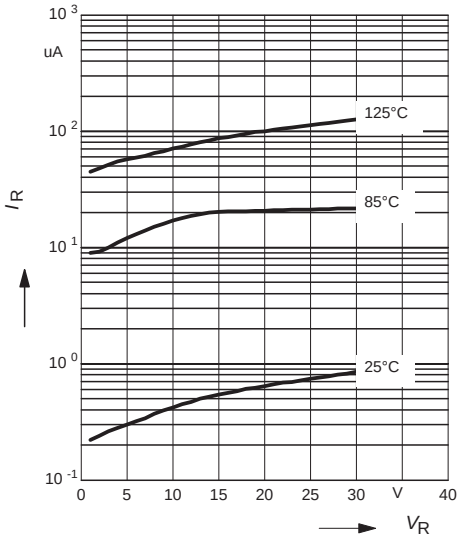
Forward current $I_F = f(V_F)$

T_A = parameter



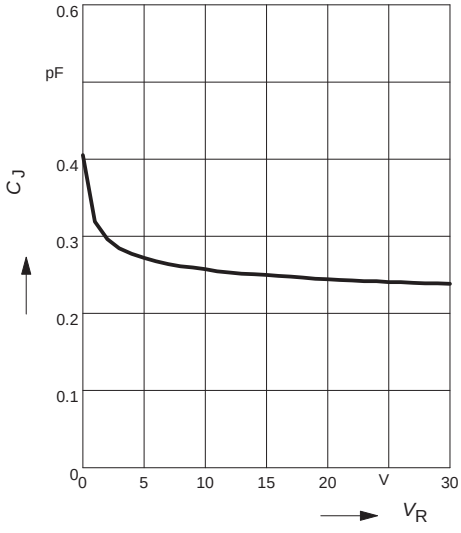
Leakage current $I_R = f(V_R)$

T_A = Parameter



Diode capacitance $C_J = f(V_R)$

f = 1MHz



Rectifier voltage $V_A = f(V_E)$

f = 900 MHz

R_L = parameter in Ω